

FJE3303H1TU Datasheet



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DiGi Electronics Part Number FJE3303H1TU-DG

Manufacturer onsemi

Manufacturer Product Number FJE3303H1TU

Description TRANS NPN 400V 1.5A TO126-3

Detailed Description Bipolar (BJT) Transistor NPN 400 V 1.5 A 4MHz 20 W

Through Hole TO-126-3



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RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FJE3303H1TU	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	1.5 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
400 V	3V @ 500mA, 1.5A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10μA (ICBO)	8 @ 500mA, 2V
Power - Max:	Frequency - Transition:
20 W	4MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-225AA, TO-126-3	TO-126-3
Base Product Number:	
FJE3303	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



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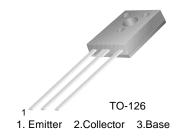
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FJE3303

High Voltage Fast-Switching NPN Power Transistor

- · High Voltage Capability
- · High Switching Speed
- Suitable for Electronic Ballast and Switching Regulator



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	1.5	A
I _{CP}	Collector Current (Pulse) *	3	А
I _B	Base Current (DC)	0.75	A
I _{BP}	Base Current (Pulse) *	1.5	А
P_{C}	Collector Dissipation (T _C = 25°C)	20	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 ~ 150	°C

^{*} Pulse Test: Pulse Width = 5ms, Duty Cycle \leq 10%

Electrical Characteristics $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV _{CBO}	Collector-Base Breakdwon Voltage	$I_C = 500 \mu A, I_E = 0$	700			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500\mu A, I_C = 0$	9			V
I _{CBO}	Collector Cut-off Current	V _{CB} = 700V, I _E = 0			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			10	μΑ
h _{FE1} h _{FE2}	DC Current Gain *	V _{CE} = 2V, I _C = 0.5A V _{CE} = 2V, I _C = 1.0A	8 5		21	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1.0A, I_B = 0.25A$ $I_C = 1.5A, I_B = 0.5A$			0.5 1.0 3.0	V V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1.0A, I_B = 0.25A$			1.0 1.2	V V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.1A$	4			MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 0.1MHz		21		pF
t _{ON}	Turn On Time	V _{CC} = 125V, I _C = 1A			1.1	μs
t _{STG}	Storge Time	$I_{B1} = 0.2A, I_{B2} = -0.2A$ $= R_1 = 125\Omega$			4.0	μs
t _F	Fall Time	11[- 12032			0.7	μs

^{*} Pulse Test: PW $\leq 300 \mu s$, Duty Cycle $\leq 2\%$

h_{FE} Classification

Classification	H1	H2
h _{FE1}	8 ~ 16	14 ~ 21

Typical Performance Characteristics

Figure 1. Static Characteristic

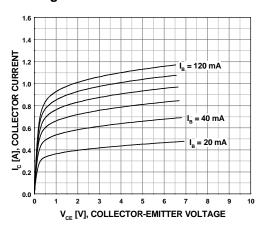


Figure 2. DC Current Gain

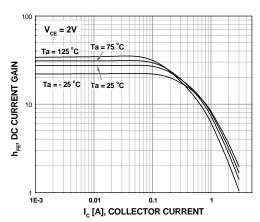


Figure 3. Collector-Emitter Saturation Voltage

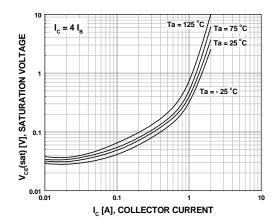


Figure 4. Base-Emitter Saturation Voltage

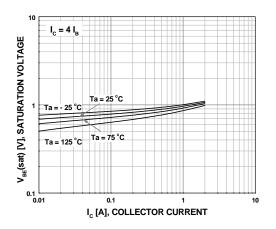


Figure 5. Resistive Load Switching Time

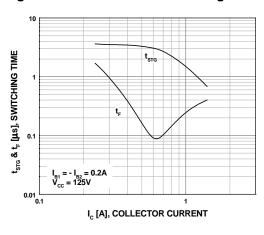
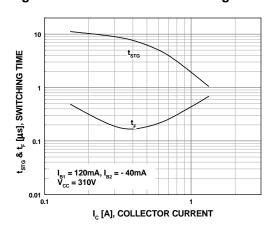


Figure 6. Resistive Load Switching Time



Typical Performance Characteristics (Continued)

Figure 7. Forward Biased Safe Operating Area

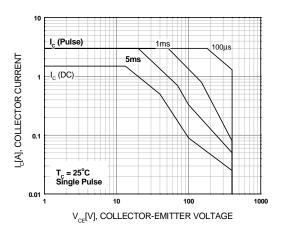
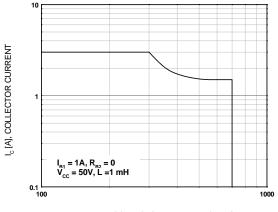
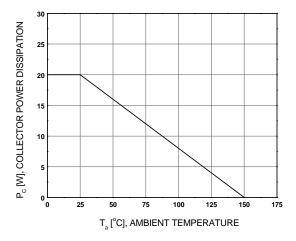


Figure 8. Reverse Biased Safe Operating Area

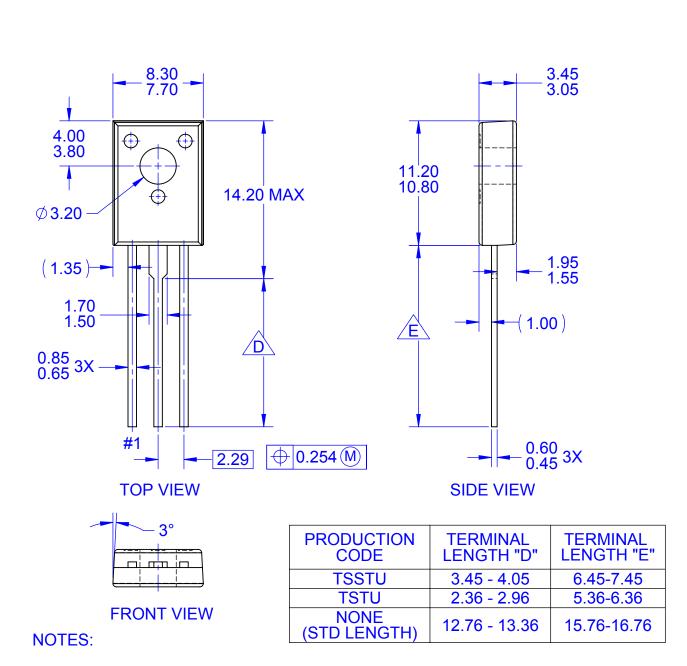


 V_{CE} [V], COLLECTOR-EMITTER VOLTAGE

Figure 9. Power Derating



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